

10/574835

IDS Dated 4/6/2006

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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. 60562.00009	SERIAL NO. New Application
LIST OF REFERENCES CITED BY APPLICANT <i>(Use several sheets if necessary)</i>			APPLICANT SAKAI et al	
			FILING DATE April 6, 2006	GROUP Art Unit 2811

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
	AA	2003/0141504	07/31/03	Kuwabara et al			
	AB						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION YES NO PART.
/A.O.A./	AC	2003-152191	05/23/2003	Japan			
/A.O.A./	AD	2001-102442	04/13/2001	Japan			xx
/A.O.A./	AE	2000-150664	05/30/2000	Japan			xx
/A.O.A./	AF	10-209453	08/07/1998	Japan			xx
/A.O.A./	AG	2004-349702	12/09/2004	Japan			xx
/A.O.A./	AH	07-335735	12/22/1995	Japan			xx
/A.O.A./	AI	05-021465	01/29/1993	Japan			xx

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

/A.O.A./	AJ	Sasaki et al, "Proposal of a Multi-Layer Channel MOSFET: the application of selective etching for Si/SiGe stacked layers," Applied Surface Science, Vol. 234, pp 270-273.
	AK	
	AL	

EXAMINER /Andrew O. Arena/ DATE CONSIDERED 12/22/2008

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.